# **BLF8G24LS-150V**; BLF8G24LS-150GV Power LDMOS transistor

**AMPLEON** 

Rev. 4 — 1 September 2015

Product data sheet

## **Product profile**

### 1.1 General description

150 W LDMOS power transistor with improved video bandwidth for base station applications at frequencies from 2300 MHz to 2400 MHz.

Table 1. Typical performance

Typical RF performance at  $T_{case} = 25$  °C in a common source class-AB production test circuit.

Test signal	f	I <sub>Dq</sub>	V <sub>DS</sub>	P <sub>L(AV)</sub>	Gp	$\eta_D$	ACPR <sub>5M</sub>
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2300 to 2400	1300	28	45	19	33	-30 <u>[1]</u>

<sup>[1] 3</sup>GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF; carrier spacing 5 MHz. Channel bandwidth is 3.84 MHz.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth (70 MHz typical)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- Design optimized for gull-wing
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

#### 1.3 Applications

RF power amplifiers for base stations and multi carrier applications in the 2300 MHz to 2400 MHz frequency range

# 2. Pinning information

Table 2. Pinning

	Z. 1 mming		
Pin	Description	Simplified outline	Graphic symbol
BLF8	G24LS-150V (SOT1244B)		
1	drain	4 1 5	4
2	gate	4 1 5	6,7 → 1
3	source [1]		2
4	decoupling lead	3	3
5	decoupling lead		aaa-003619
6	n.c.		
7	n.c.	6 2 7	
BLF8	G24LS-150GV (SOT1244C)		•
1	drain	4 1 5	4
2	gate	4 1 5	6,7 → 1 → 4,5
3	source [1]		2
4	decoupling lead		3
5	decoupling lead	6 2 7	aaa-003619
6	n.c.	6 2   7	
7	n.c.		

<sup>[1]</sup> Connected to flange.

# 3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BLF8G24LS-150V	-	earless flanged ceramic package; 6 leads	SOT1244B	
BLF8G24LS-150GV	-	earless flanged ceramic package; 6 leads	SOT1244C	

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

#### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	$T_{case}$ = 80 °C; $P_L$ = 45 W	0.30	K/W

#### 6. Characteristics

#### Table 6. DC characteristics

 $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.16 \text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 216 mA	1.5	1.9	2.3	V
$V_{GSq}$	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 1300 mA	1.6	2	2.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 28 V	-	-	4.5	μА
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$	-	40	-	A
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	450	nA
g <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 10.8 A	-	16	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 7.56 \text{ A}$	-	0.06	-	Ω

#### Table 7. RF characteristics

Test signal: 2-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on the CCDF, carrier spacing 5 MHz;  $f_1$  = 2302.5 MHz;  $f_2$  = 2307.5 MHz;  $f_3$  = 2392.5 MHz;  $f_4$  = 2397.5 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA;  $T_{case}$  = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G <sub>p</sub>	power gain	P <sub>L(AV)</sub> = 45 W	17.5	19	-	dB
RLin	input return loss	P <sub>L(AV)</sub> = 45 W	-	-10	-7	dB
$\eta_{D}$	drain efficiency	P <sub>L(AV)</sub> = 45 W	29	33	-	%
ACPR <sub>5M</sub>	adjacent channel power ratio (5 MHz)	P <sub>L(AV)</sub> = 45 W	-	-30	-27	dBc

#### 7. Test information

#### 7.1 Ruggedness in class-AB operation

The BLF8G24LS-150V and BLF8G24LS-150GV are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS} = 28 \text{ V}$ ;  $I_{Dq} = 1300 \text{ mA}$ ;  $P_L = 150 \text{ W}$  (CW); f = 2300 MHz.

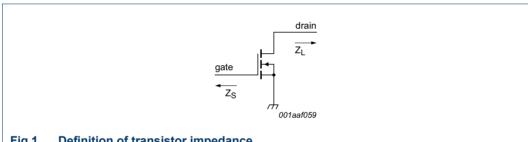
# 7.2 Impedance information

Table 8. **Typical impedance** 

Measured load-pull data;  $I_{Dq} = 1300 \text{ mA}$ ;  $V_{DS} = 28 \text{ V}$ .

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]
(MHz)	(Ω)	(Ω)
BLF8G24LS-150V		
2300	1.25 – j4.11	2.95 – j1.20
2400	2.34 – j5.50	2.88 – j1.31
2500	5.65 – j6.35	2.80 – j1.35
BLF8G24LS-150GV		
2300	1.29 – j5.78	3.13 – j3.26
2400	2.15 – j7.09	2.78 – j3.44
2500	6.61 – j7.57	2.98 – j3.66

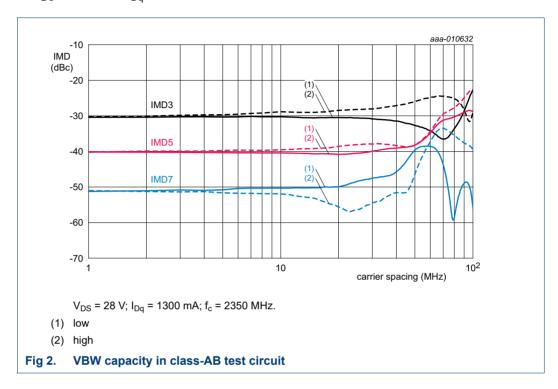
[1]  $Z_S$  and  $Z_L$  defined in Figure 1.



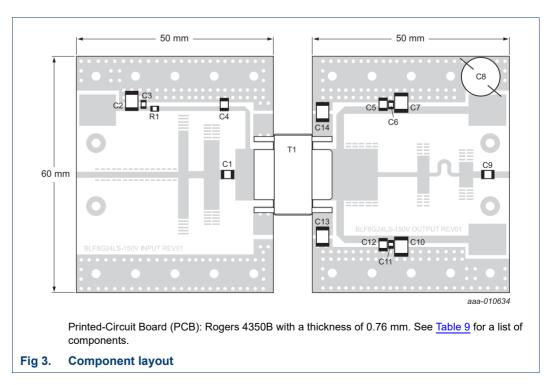
**Definition of transistor impedance** Fig 1.

#### 7.3 VBW in a class-AB operation

The BLF8G24LS-150V shows 70 MHz (typical) video bandwidth (IMD third-order intermodulation inflection point) in a class-AB test circuit in the 2.3 GHz to 2.4 GHz band at  $V_{DS}$  = 28 V and  $I_{Dg}$  = 1.3 A.



### 7.4 Test circuit



BLF8G24LS-150V\_8G24LS-150GV#4

Table 9. List of components

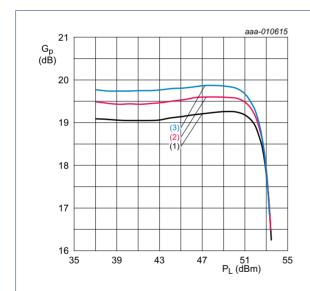
See Figure 3 for component layout.

Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	1.2 pF [1]	ATC 800B
C2	multilayer ceramic chip capacitor	1 μF	Murata
C3	multilayer ceramic chip capacitor	100 nF [2]	Murata
C4, C5, C9, C12	multilayer ceramic chip capacitor	24 pF [1]	ATC 800B
C6, C11	multilayer ceramic chip capacitor	220 nF [2]	Murata
C7, C10, C13, C14	multilayer ceramic chip capacitor	4.7 μF, 50 V	Murata
C8	electrolytic capacitor	> 470 μF, 63 V	
R1	chip resistor	4.7 Ω, 1 % tolerance	SMD 0805
T1	transistor	-	Ampleon BLF8G24LS-150V

- [1] American Technical Ceramics type 800B or capacitor of same quality.
- [2] Murata or capacitor of same quality.

### 7.5 Graphical data

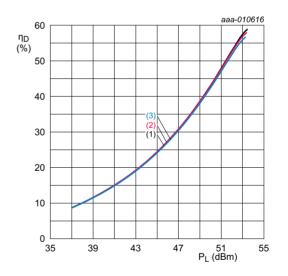
#### 7.5.1 Pulsed CW



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 4. Power gain as a function of output power; typical values

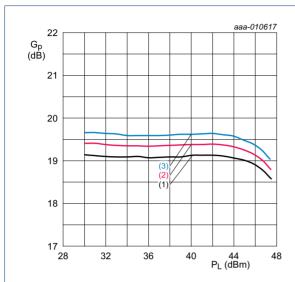


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 5. Drain efficiency as a function of out power; typical values

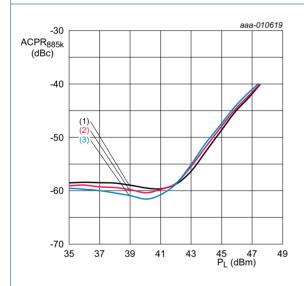
#### 7.5.2 IS-95



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

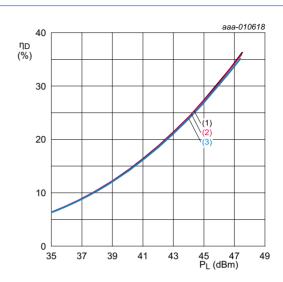
Fig 6. Power gain as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

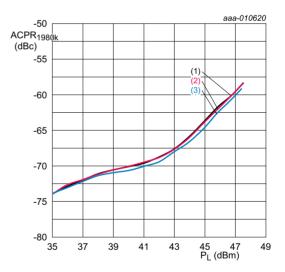
Fig 8. Adjacent channel power ratio (885 kHz) as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 7. Drain efficiency as a function of output power; typical values



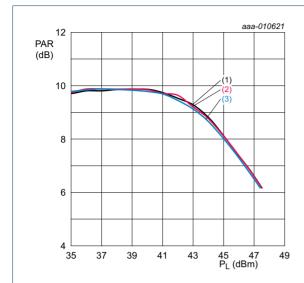
 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 9. Adjacent channel power ratio (1980 kHz) as a function of output power; typical values

# BLF8G24LS-150(G)V

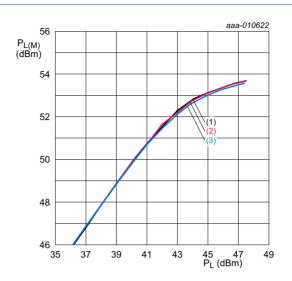
**Power LDMOS transistor** 



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 10. Peak-to-average ratio as a function of output power; typical values

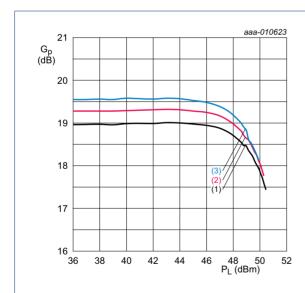


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 11. Peak output power as a function of output power; typical values

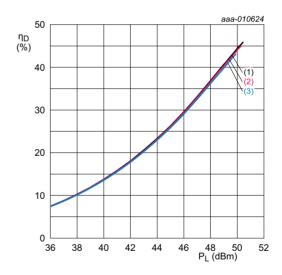
#### 7.5.3 1-Carrier W-CDMA



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 12. Power gain as a function of output power; typical values



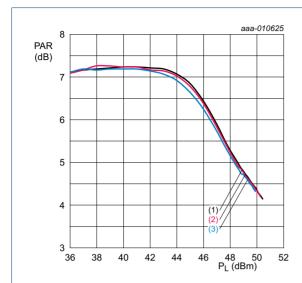
 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 13. Drain efficiency as a function of output power; typical values

# BLF8G24LS-150(G)V

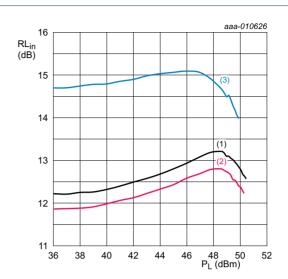
**Power LDMOS transistor** 



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 14. Peak-to-average ratio as a function of output power; typical values

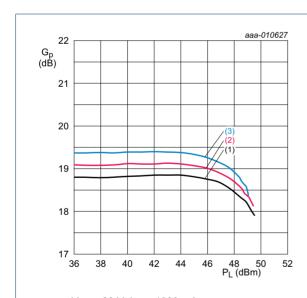


 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2302.5 MHz
- (2) f = 2350 MHz
- (3) f = 2397.5 MHz

Fig 15. Input return loss as a function of output power; typical values

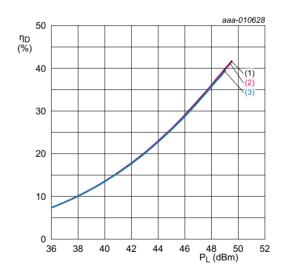
#### 7.5.4 2-Carrier W-CDMA



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

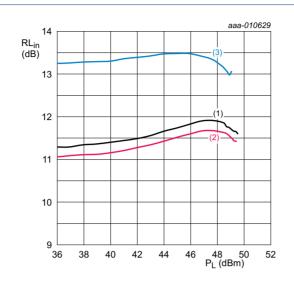
Fig 16. Power gain as a function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

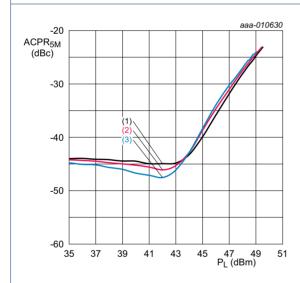
Fig 17. Drain efficiency as a function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

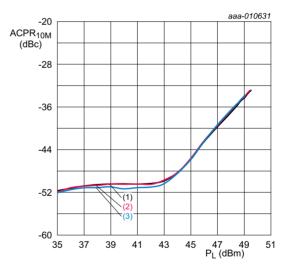
Fig 18. Input return loss as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 19. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2305 MHz
- (2) f = 2350 MHz
- (3) f = 2395 MHz

Fig 20. Adjacent channel power ratio (10 MHz) as a function of output power; typical values

# 8. Package outline

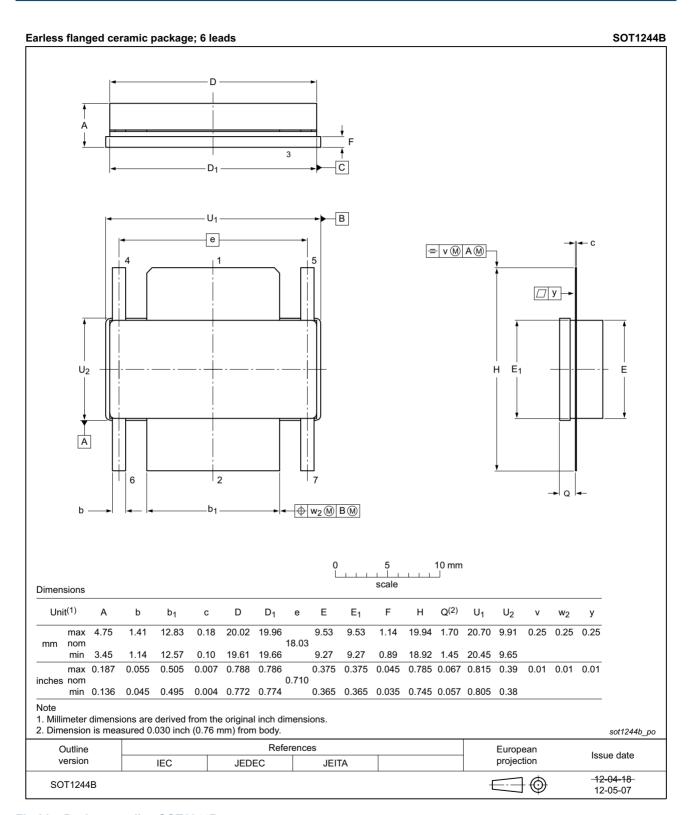


Fig 21. Package outline SOT1244B

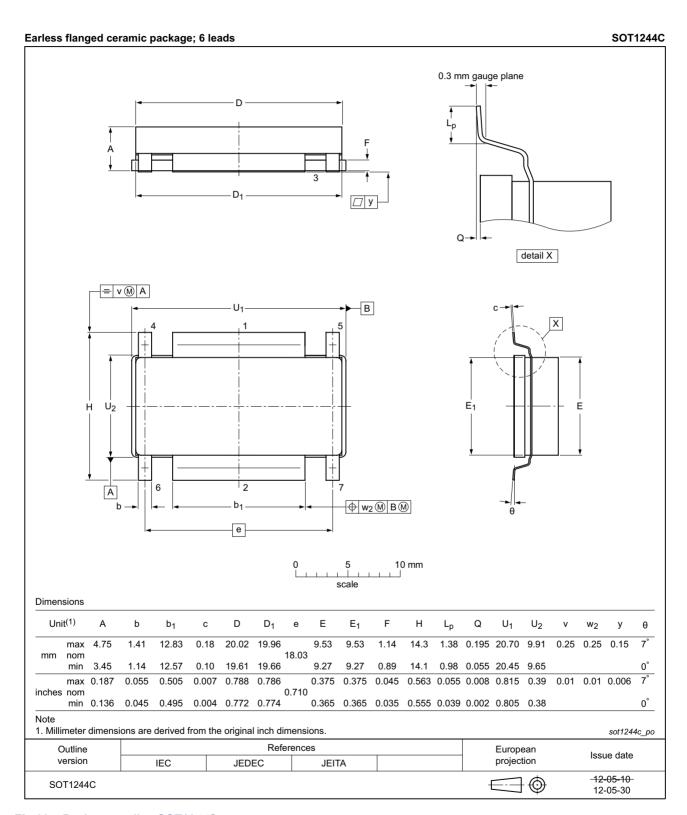


Fig 22. Package outline SOT1244C

# 9. Handling information

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

### 10. Abbreviations

Table 10. Abbreviations

Acronym	Description	
3GPP	3rd Generation Partnership Project	
CCDF	Complementary Cumulative Distribution Function	
CW	Continuous Wave	
DPCH	Dedicated Physical CHannel	
ESD	ElectroStatic Discharge	
IS-95	Interim Standard 95	
LDMOS	Laterally Diffused Metal Oxide Semiconductor	
MTF	Median Time to Failure	
PAR	Peak-to-Average Ratio	
SMD	Surface Mounted Device	
VBW	Video BandWidth	
VSWR	Voltage Standing Wave Ratio	
W-CDMA	Wideband Code Division Multiple Access	

# 11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF8G24LS-150V_8G24LS-150GV#4	20150901	Product data sheet		BLF8G24LS-150V_ 8G24LS-150GV v.3
Modifications:	<ul> <li>The format of this document has been redesigned to comply with the new identity guidelines of Ampleon.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>			
BLF8G24LS-150V_8G24LS-150GV v.3	20140512	Product data sheet	-	BLF8G24LS-150V_ 8G24LS-150GV v.2
BLF8G24LS-150V_8G24LS-150GV v.2	20140224	Objective data sheet	-	BLF8G24LS-150V_ 8G24LS-150GV v.1
BLF8G24LS-150V_8G24LS-150GV v.1	20131104	Objective data sheet	-	-

# 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BLF8G24LS-150V 8G24LS-150GV#4

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# **BLF8G24LS-150(G)V**

**Power LDMOS transistor** 

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#### 13. Contact information

For more information, please visit: http://www.ampleon.com

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# **AMPLEON**

# BLF8G24LS-150(G)V

**Power LDMOS transistor** 

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